

SOT-23


1. BASE
2. EMITTER
3. COLLECTOR

Marking: 2X

Features

- Power Dissipation of 300mW
- High Stability and High Reliability

Maximum Ratings

(Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter -Base Voltage	V_{EBO}	6	V
Collector Current-Continuous	I_C	600	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55-+150	°C
Thermal resistance From junction to ambient	$R_{\theta JA}$	417	°C/W

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified).

Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$		100	nA
Collector cut-off current	I_{CEX}	$V_{CE}=35V, V_{EB(off)}=0.4V$		100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=0.1mA$	20		
	$h_{FE(2)}$	$V_{CE}=1V, I_C=1mA$	40		
	$h_{FE(3)}$	$V_{CE}=1V, I_C=10mA$	80		
	$h_{FE(4)}$	$V_{CE}=1V, I_C=150mA$	100	300	
	$h_{FE(5)}$	$V_{CE}=1V, I_C=500mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=150mA, I_B=15mA$		0.40	V
		$I_C=500mA, I_B=50mA$		0.75	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C=150mA, I_B=15mA$		0.95	V
		$I_C=500mA, I_B=50mA$		1.20	V
Transition frequency	f_T	$V_{CE}=10V, I_C=20mA, f=100MHz$	250		MHz
Delay time	t_d	$V_{CC}=30V, V_{BE(off)}=-2V, I_C=150mA, I_{B1}=15mA$		15	nS
Rise time	t_r			20	nS
Storage time	t_s	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		225	nS
Fall time	t_f			60	nS

